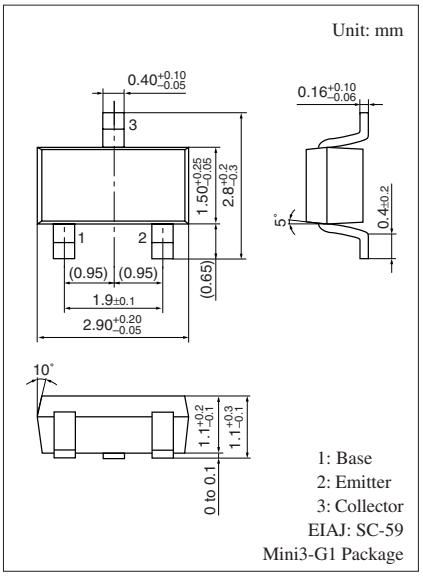
2SB0792 (2SB792), 2SB0792A (2SB792A)

Silicon PNP epitaxial planar type

For high breakdown voltage low-noise amplification

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- Low noise voltage NV
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing



Marking Symbol:

- 2SB0792: I
- 2SB0792A: 2F

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0792	V_{CBO}	−150	V
	2SB0792A		−185	
Collector-emitter voltage (Base open)	2SB0792	V_{CEO}	−150	V
	2SB0792A		−185	
Emitter-base voltage (Collector open)		V_{EBO}	−5	V
Collector current		I_C	−50	mA
Peak collector current		I_{CP}	−100	mA
Collector power dissipation		P_C	200	mW
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0792	V_{CEO}	$I_C = -100$ μA, $I_B = 0$	−150			V
	2SB0792A			−185			
Emitter-base voltage (Collector open)		V_{EBO}	$I_E = -10$ μA, $I_C = 0$	−5			V
Collector-base cutoff current (Emitter open)		I_{CBO}	$V_{CB} = -100$ V, $I_E = 0$			−1	μA
Forward current transfer ratio *	2SB0792	h_{FE}	$V_{CE} = -5$ V, $I_C = -10$ mA	130		450	—
	2SB0792A			130		330	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = -30$ mA, $I_B = -3$ mA			−1	V
Transition frequency		f_T	$V_{CB} = -10$ V, $I_E = 10$ mA, f = 200 MHz		200		MHz
Collector output capacitance (Common base, input open circuited)		C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		4		pF
Noise voltage		NV	$V_{CE} = -10$ V, $I_C = -1$ mA, $G_V = 80$ dB $R_g = 100$ kΩ, Function = FLAT		150		mV

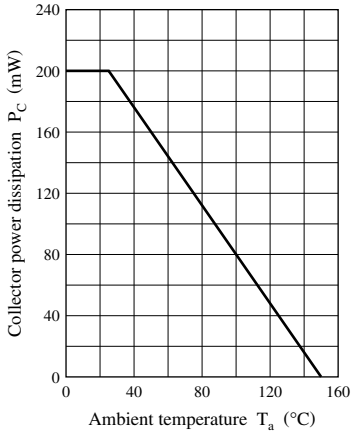
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

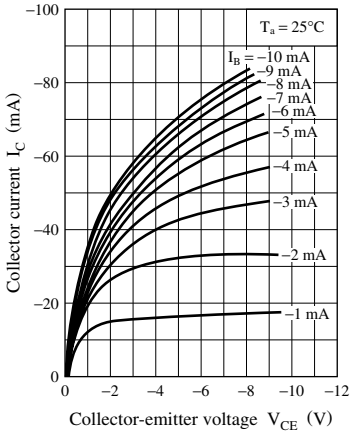
Rank		R	S	T
h_{FE}		130 to 220	185 to 330	260 to 450
Marking symbol	2SB0792	IR	IS	IT
	2SB0792A	2FR	2FS	—

Note) The part numbers in the parenthesis show conventional part number.

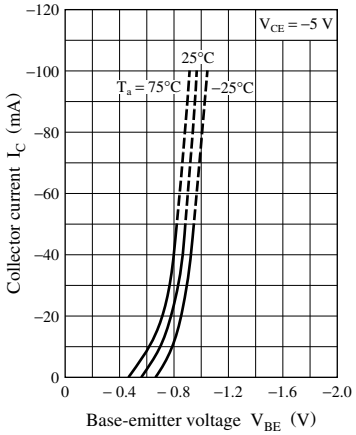
P_C — T_a



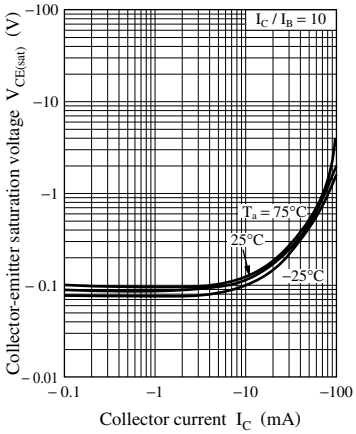
I_C — V_{CE}



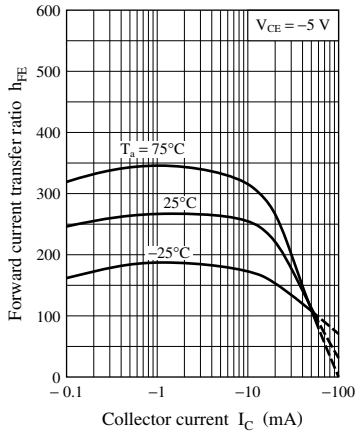
I_C — V_{BE}



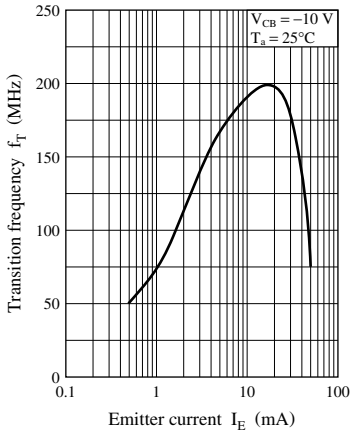
$V_{CE(sat)}$ — I_C



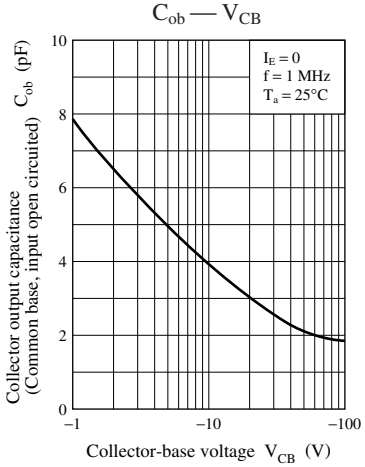
h_{FE} — I_C



f_T — I_E



C_{ob} — V_{CB}



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